



**THE DATASHEET OF  
IPP060N06NAKSA1**

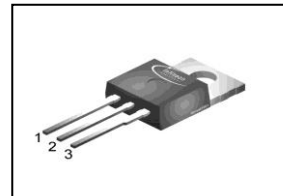


**OptiMOS™ Power-Transistor**
**Features**

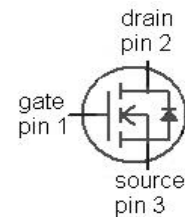
- Optimized for high performance SMPS, e.g. sync. rec.
- 100% avalanche tested
- Superior thermal resistance
- N-channel
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

**Product Summary**

|                  |     |    |
|------------------|-----|----|
| $V_{DS}$         | 60  | V  |
| $R_{DS(on),max}$ | 6.0 | mΩ |
| $I_D$            | 45  | A  |
| $Q_{OSS}$        | 32  | nC |
| $Q_G(0V..10V)$   | 27  | nC |


**PG-TO220-3**


| Type       | Package    | Marking |
|------------|------------|---------|
| IPP060N06N | PG-TO220-3 | 060N06N |


**Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified**

| Parameter                                    | Symbol        | Conditions  | Value | Unit |
|--|---------------|---|-------|------|
| Continuous drain current                     | $I_D$         | $V_{GS}=10\text{ V}, T_C=25\text{ °C}$                        | 45    | A    |
|  |               | $V_{GS}=10\text{ V}, T_C=100\text{ °C}$                       | 45    |      |
|  |               | $V_{GS}=10\text{ V}, T_C=25\text{ °C}, R_{thJA}=50\text{K/W}$ | 17    |      |
| Pulsed drain current <sup>2)</sup>           | $I_{D,pulse}$ | $T_C=25\text{ °C}$  | 180   |      |
| Avalanche energy, single pulse <sup>3)</sup> | $E_{AS}$      | $I_D=45\text{ A}, R_{GS}=25\text{ Ω}$                         | 60    | mJ   |
| Gate source voltage                          | $V_{GS}$      |   | ±20   | V    |

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> See figure 3 for more detailed information

<sup>3)</sup> See figure 13 for more detailed information

<sup>4)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

**Maximum ratings**, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol                | Conditions  | Value       | Unit |
|-------------------------------------|-----------------------|---|-------------|------|
| Power dissipation                   | $P_{\text{tot}}$      | $T_C=25\text{ °C}$                                      | 83          | W    |
|                                     |                       | $T_A=25\text{ °C}$ ,<br>$R_{\text{thJA}}=50\text{ K/W}$ | 3.0         |      |
| Operating and storage temperature   | $T_j, T_{\text{stg}}$ |   | -55 ... 175 | °C   |
| IEC climatic category; DIN IEC 68-1 |                       |   | 55/175/56   |      |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|                                     |                   |  |   |   |     |     |
|-------------------------------------|-------------------|--|---|---|-----|-----|
| Thermal resistance, junction - case | $R_{\text{thJC}}$ | bottom                                       | - | - | 1.8 | K/W |
| Device on PCB                       | $R_{\text{thJA}}$ | minimal footprint                            | - | - | 62  |     |
|                                     |                   | 6 cm <sup>2</sup> cooling area <sup>4)</sup> | - | - | 40  |     |

**Electrical characteristics**, at  $T_j=25\text{ °C}$ , unless otherwise specified

**Static characteristics**

|                                  |                             |   |     |     |     |               |
|----------------------------------|-----------------------------|---|-----|-----|-----|---------------|
| Drain-source breakdown voltage   | $V_{(\text{BR})\text{DSS}}$ | $V_{\text{GS}}=0\text{ V}$ , $I_{\text{D}}=1\text{ mA}$                               | 60  | -   | -   | V             |
| Gate threshold voltage           | $V_{\text{GS(th)}}$         | $V_{\text{DS}}=V_{\text{GS}}$ , $I_{\text{D}}=36\text{ }\mu\text{A}$                  | 2.1 | 2.8 | 3.3 |               |
| Zero gate voltage drain current  | $I_{\text{DSS}}$            | $V_{\text{DS}}=60\text{ V}$ , $V_{\text{GS}}=0\text{ V}$ ,<br>$T_j=25\text{ °C}$      | -   | 0.5 | 1   | $\mu\text{A}$ |
|                                  |                             | $V_{\text{DS}}=60\text{ V}$ , $V_{\text{GS}}=0\text{ V}$ ,<br>$T_j=125\text{ °C}$     | -   | 10  | 100 |               |
| Gate-source leakage current      | $I_{\text{GSS}}$            | $V_{\text{GS}}=20\text{ V}$ , $V_{\text{DS}}=0\text{ V}$                              | -   | 10  | 100 | nA            |
| Drain-source on-state resistance | $R_{\text{DS(on)}}$         | $V_{\text{GS}}=10\text{ V}$ , $I_{\text{D}}=45\text{ A}$                              | -   | 5.2 | 6   | m $\Omega$    |
|                                  |                             | $V_{\text{GS}}=6\text{ V}$ , $I_{\text{D}}=12\text{ A}$                               | -   | 6.7 | 9   |               |
| Gate resistance                  | $R_{\text{G}}$              |   | -   | 1.5 | 2.3 | $\Omega$      |
| Transconductance                 | $g_{\text{fs}}$             | $ V_{\text{DS}} >2 I_{\text{D}} R_{\text{DS(on)max}}$ ,<br>$I_{\text{D}}=45\text{ A}$ | 36  | 73  | -   | S             |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Dynamic characteristics**

|                              |              |  |   |      |      |    |
|------------------------------|--------------|--|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=30\text{ V}, f=1\text{ MHz}$                            | - | 2000 | 2500 | pF |
| Output capacitance           | $C_{oss}$    |  | - | 490  | 613  |    |
| Reverse transfer capacitance | $C_{rss}$    |  | - | 22   | 44   |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=30\text{ V}, V_{GS}=10\text{ V}, I_D=45\text{ A}, R_{G,ext,ext}=3\ \Omega$ | - | 12   | -    | ns |
| Rise time                    | $t_r$        |  | - | 12   | -    |    |
| Turn-off delay time          | $t_{d(off)}$ |  | - | 20   | -    |    |
| Fall time                    | $t_f$        |  | - | 7    | -    |    |

**Gate Charge Characteristics<sup>5)</sup>**

|                              |               |   |   |     |    |    |
|------------------------------|---------------|---|---|-----|----|----|
| Gate to source charge        | $Q_{gs}$      | $V_{DD}=30\text{ V}, I_D=45\text{ A}, V_{GS}=0\text{ to }10\text{ V}$ | - | 9   | -  | nC |
| Gate charge at threshold     | $Q_{g(th)}$   |   | - | 5   | -  |    |
| Gate to drain charge         | $Q_{gd}$      |   | - | 5   | 7  |    |
| Switching charge             | $Q_{sw}$      |   | - | 9   | -  |    |
| Gate charge total            | $Q_g$         |   | - | 27  | 32 |    |
| Gate plateau voltage         | $V_{plateau}$ |   | - | 4.8 | -  | V  |
| Gate charge total, sync. FET | $Q_{g(sync)}$ | $V_{DS}=0.1\text{ V}, V_{GS}=0\text{ to }10\text{ V}$                 | - | 24  | -  | nC |
| Output charge                | $Q_{oss}$     | $V_{DD}=30\text{ V}, V_{GS}=0\text{ V}$                               | - | 32  | -  |    |

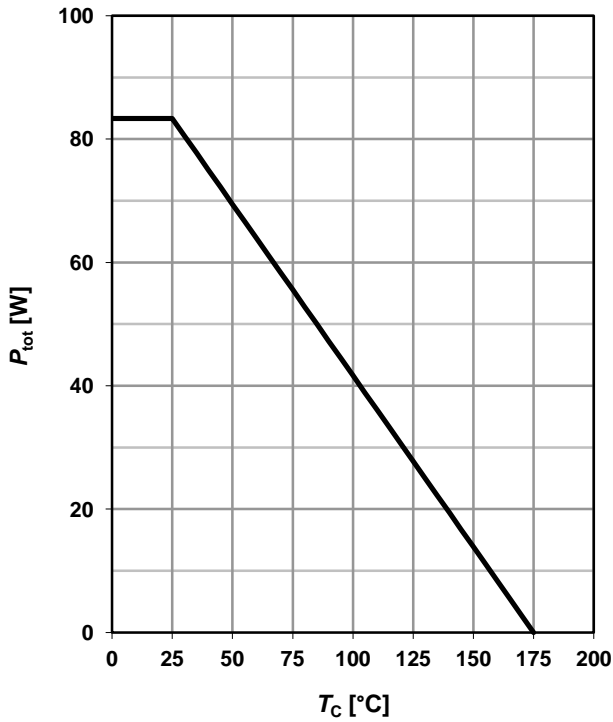
**Reverse Diode**

|                                  |               |  |   |     |     |    |
|----------------------------------|---------------|--|---|-----|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ }^\circ\text{C}$                                       | - | -   | 45  | A  |
| Diode pulse current              | $I_{S,pulse}$ |  | - | -   | 180 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=45\text{ A}, T_j=25\text{ }^\circ\text{C}$   | - | 1.0 | 1.2 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=30\text{ V}, I_F=45\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$ | - | 32  | 51  | ns |
| Reverse recovery charge          | $Q_{rr}$      |  | - | 28  | -   | nC |

<sup>5)</sup> See figure 16 for gate charge parameter definition

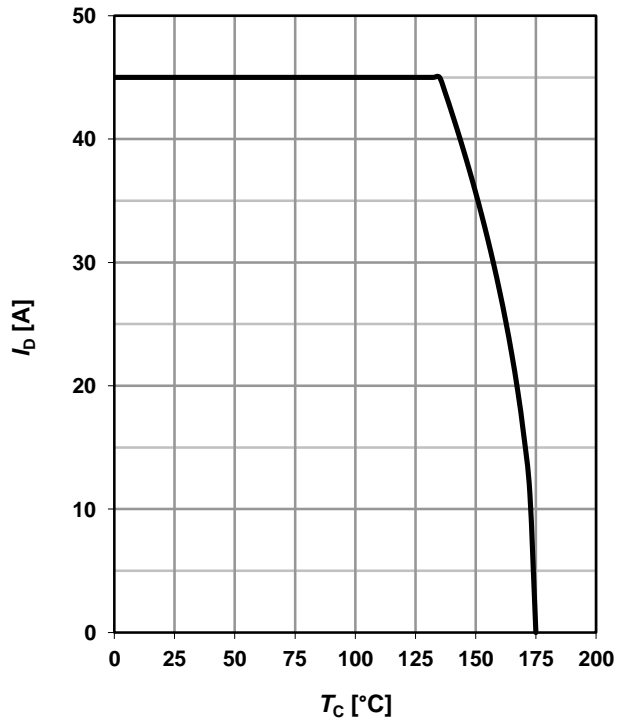
**1 Power dissipation**

$P_{tot}=f(T_C)$



**2 Drain current**

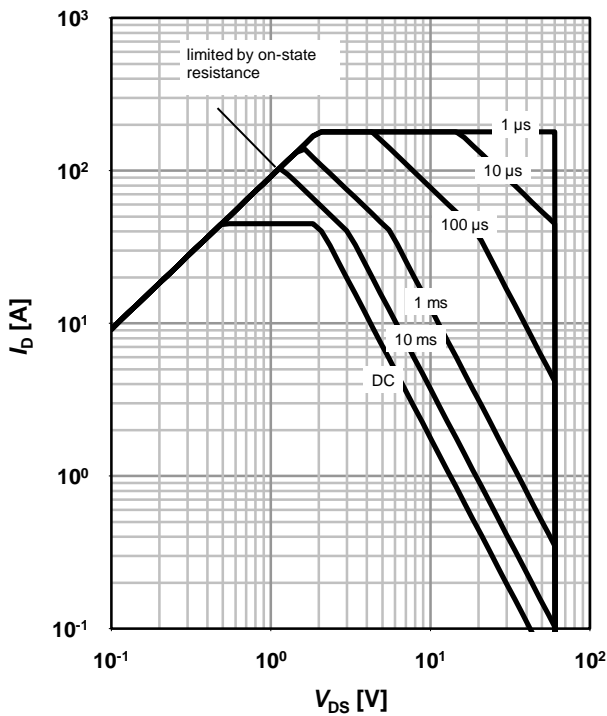
$I_D=f(T_C); V_{GS} \geq 10\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

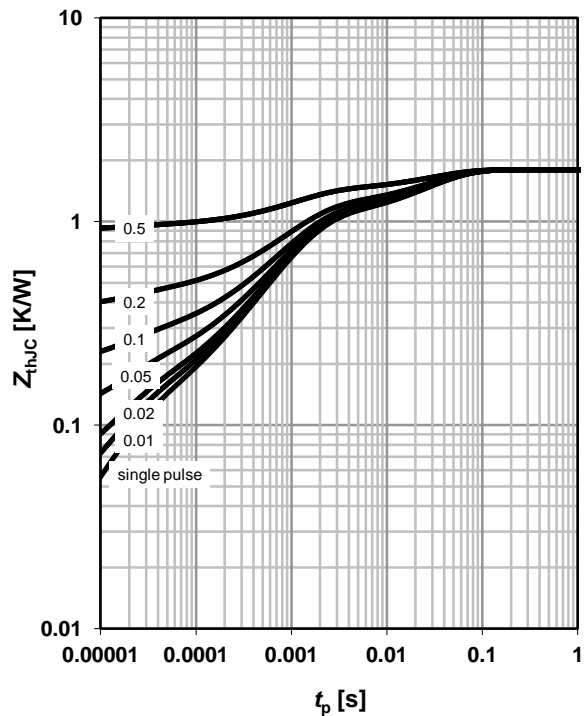
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

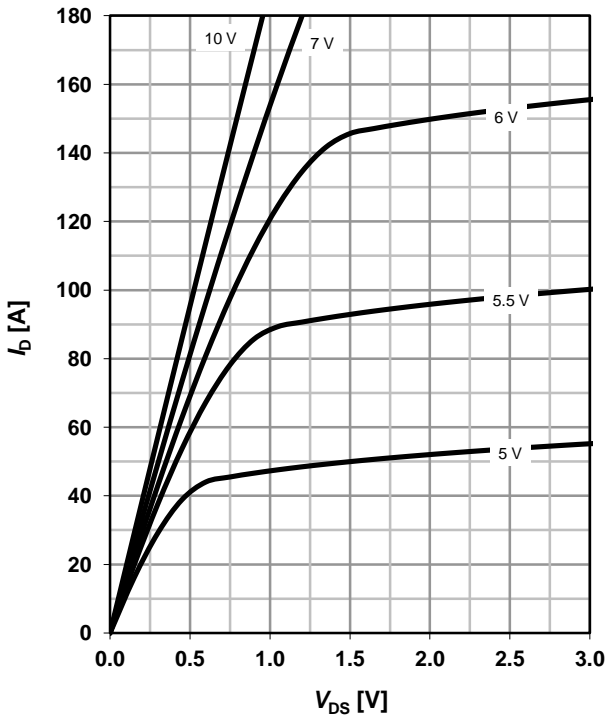
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ °C}$

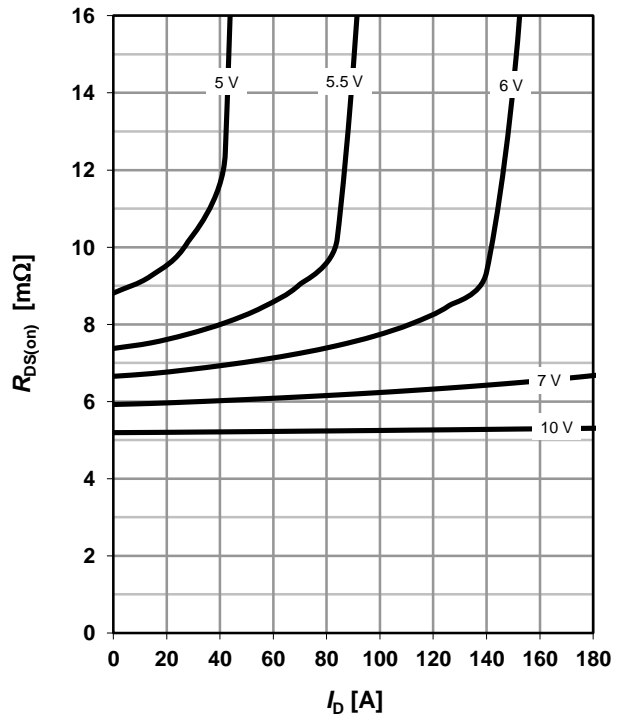
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ °C}$

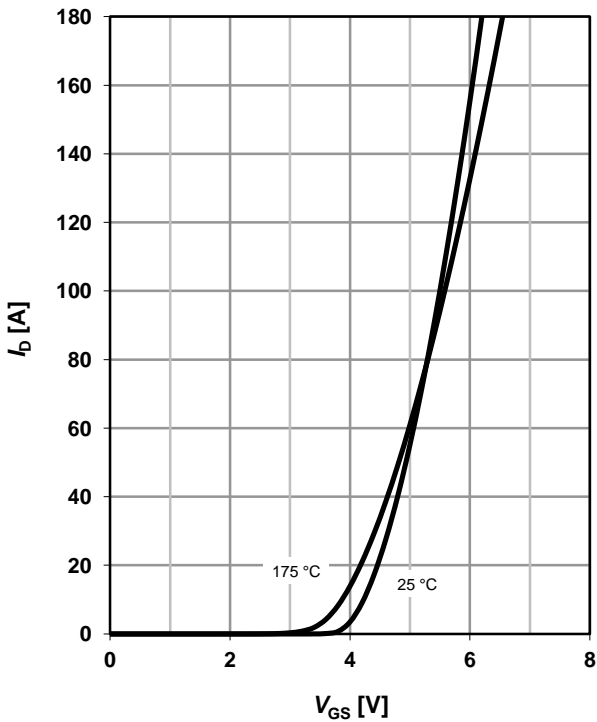
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

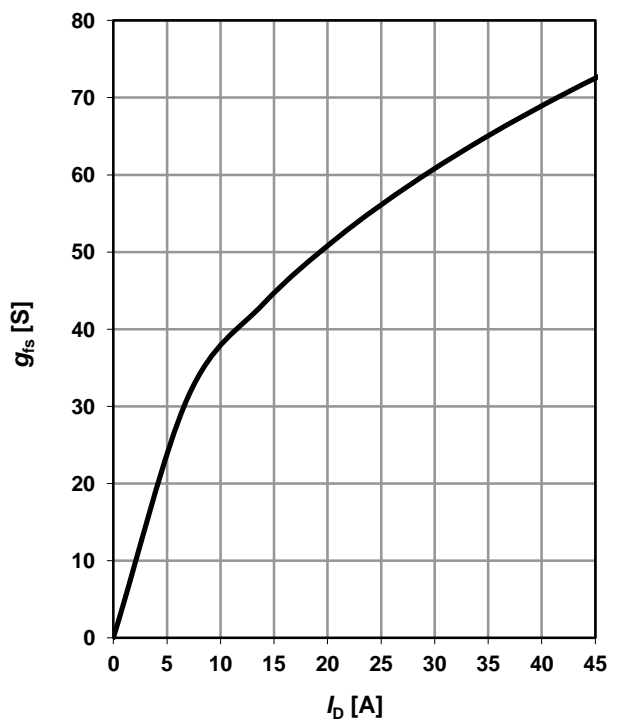
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



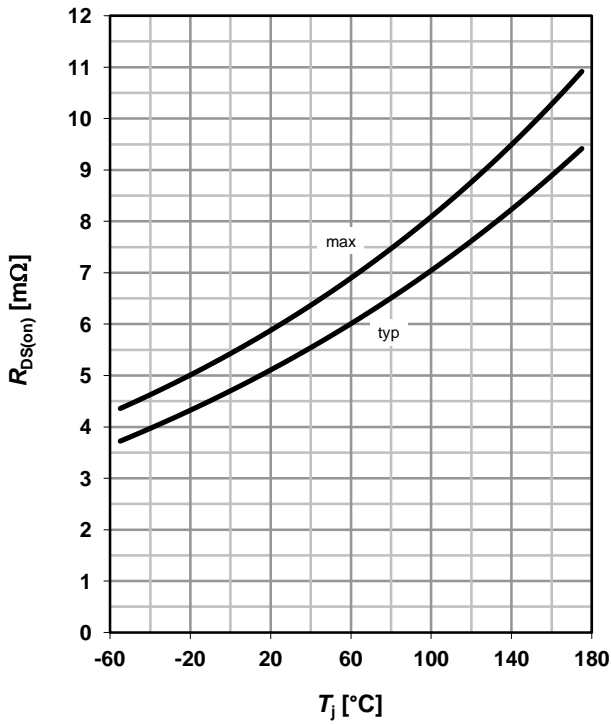
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ °C}$



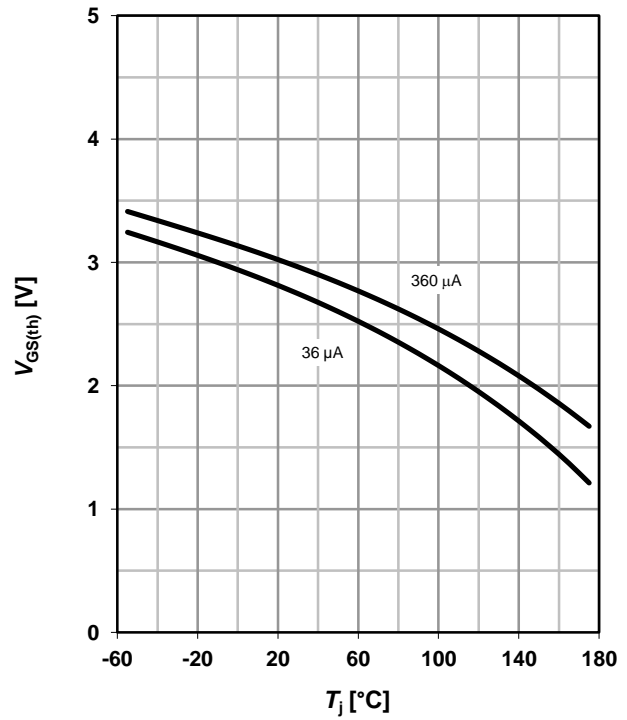
**9 Drain-source on-state resistance**

$R_{DS(on)}=f(T_j); I_D=45\text{ A}; V_{GS}=10\text{ V}$



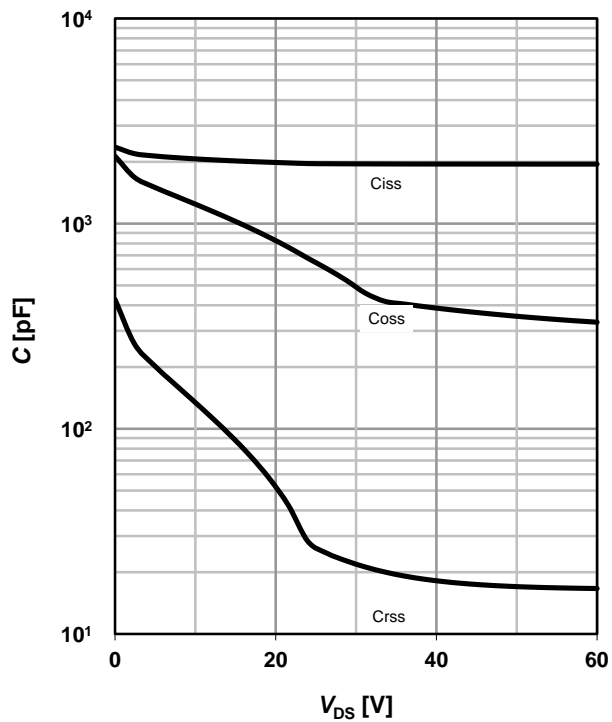
**10 Typ. gate threshold voltage**

$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}$



**11 Typ. capacitances**

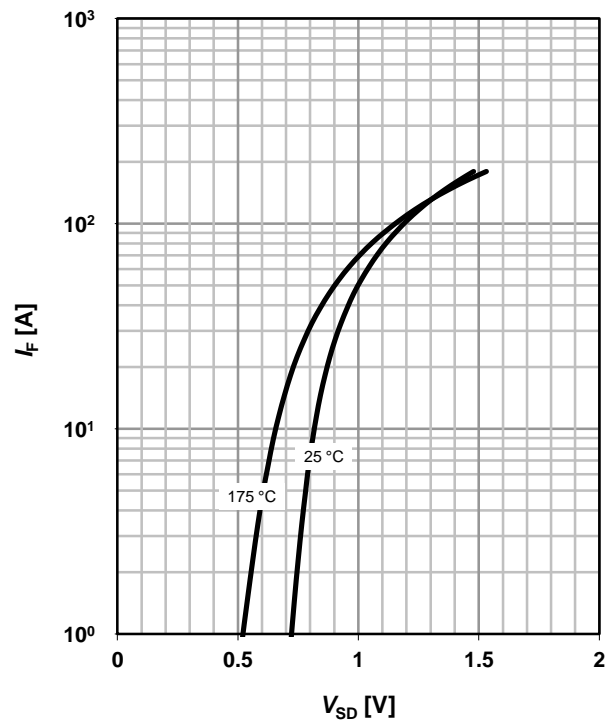
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

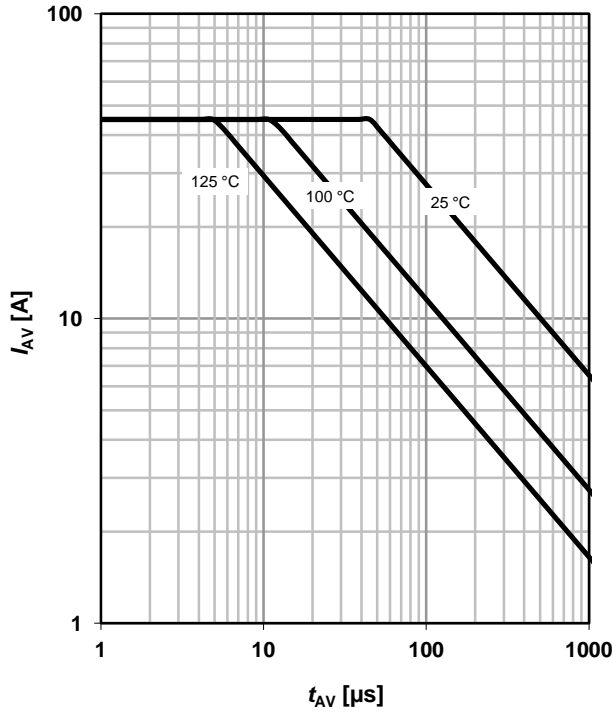
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

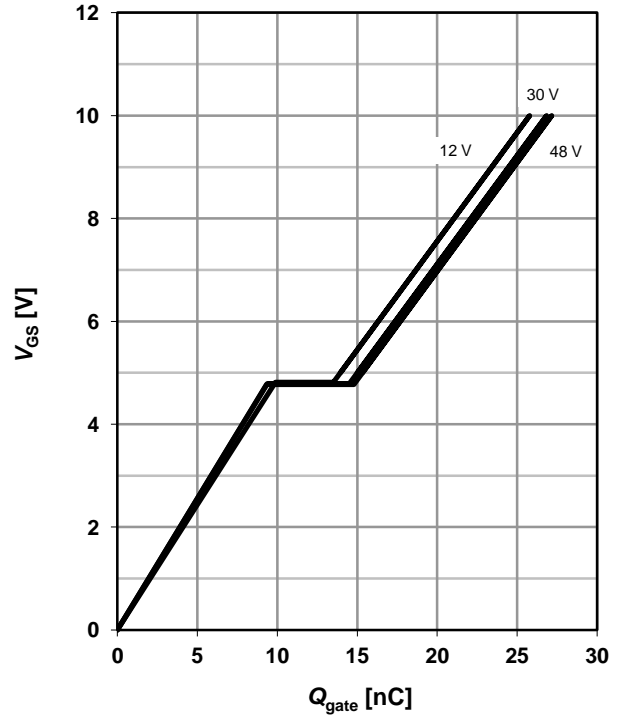
parameter:  $T_{j(\text{start})}$



**14 Typ. gate charge**

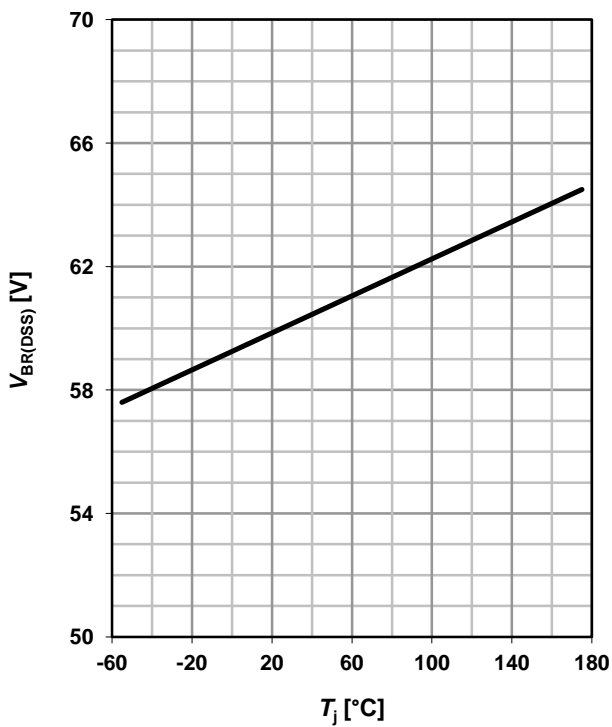
$V_{GS}=f(Q_{\text{gate}}); I_D=45 \text{ A pulsed}$

parameter:  $V_{DD}$

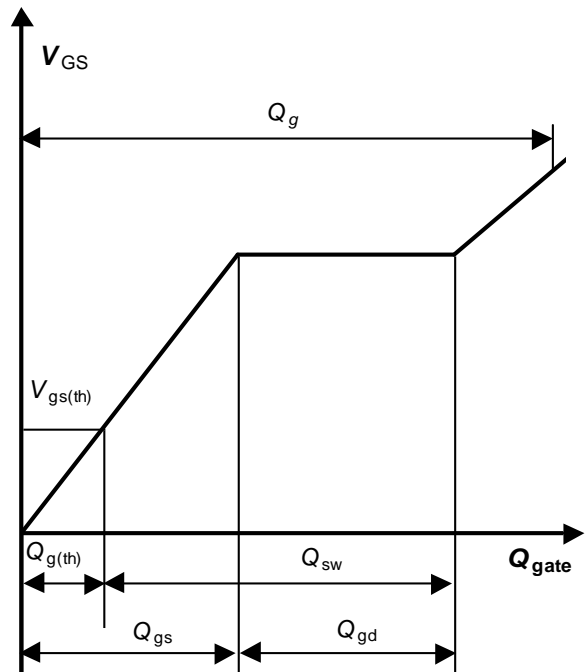


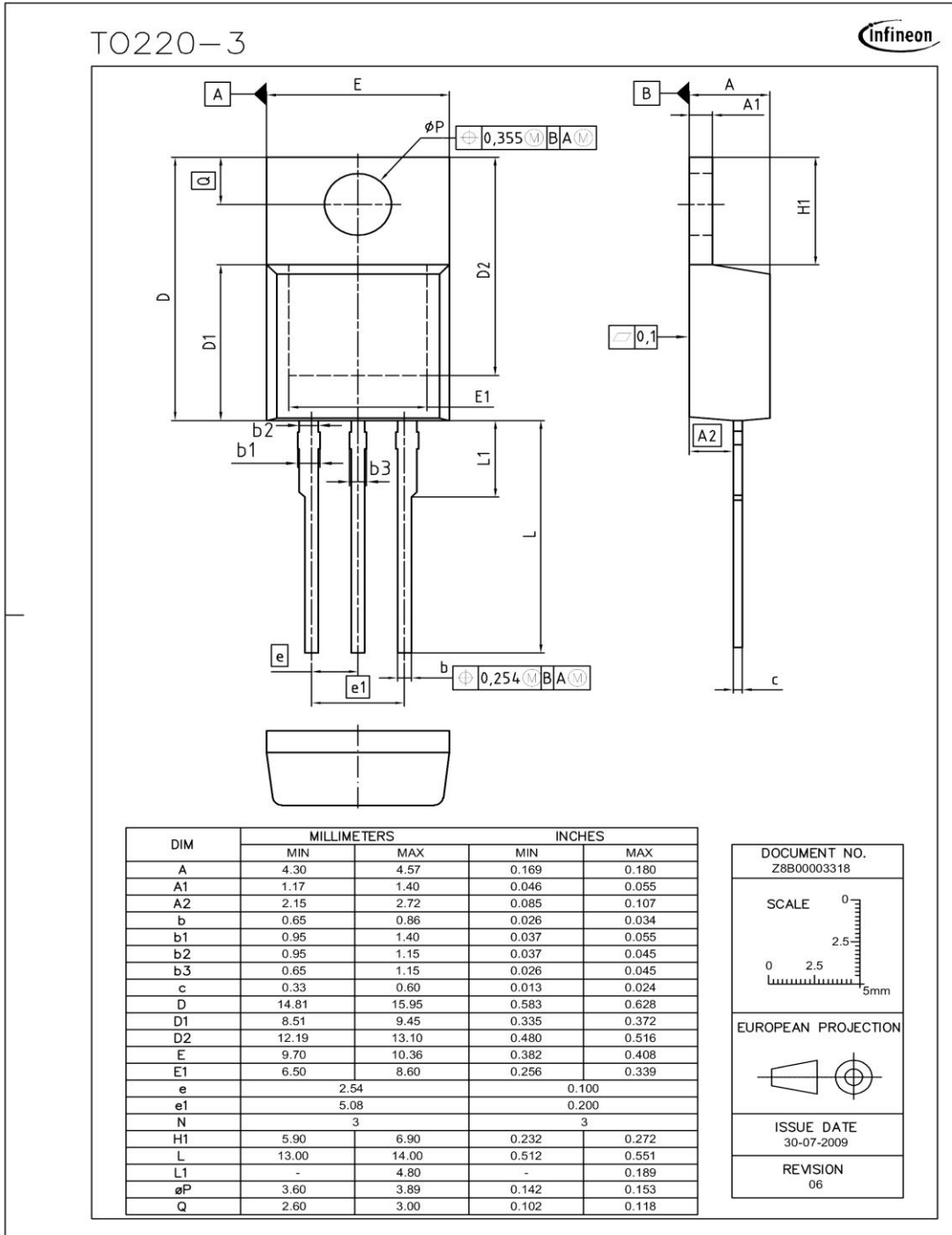
**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$



**16 Gate charge waveforms**





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